



XVME-113

RAM/ROM/Flash Memory Module

FEATURES

- Twenty-four 32-pin memory sockets
- Full 32-bit VMEbus slave interface
- Two independently configurable memory banks
- Real Time Clock
- Read back configuration
- Battery backup for CMOS RAM devices and Real-Time Clock
- Power-down memory protection circuitry
- Completely user-configurable to allow a variety of 32-pin memory device speeds and types to be used

The XVME-113 RAM/ROM Memory Module is a double-high, VMEbus compatible board. It can accommodate up to 12 MB of RAM, 24 MB of EPROM, 12 MB of EEPROM or 12 MB of FLASH.

The XVME-113 has twenty-four 32-pin JEDEC sockets that are logically arranged as two banks. Bank one contains 16 memory sites, and bank two contains 8 memory sites. Each bank is designed to employ memory devices of the same type and speed. Each bank can also be independently configured (via jumpers and switches) in terms of:

- VMEbus address (within Standard or Extended address space)
- Address modifiers
- Memory device speed, and type

The XVME-113 is designed with an on-board battery backup circuit to provide power to CMOS RAM devices in the event of a power failure. The module also provides power-down memory protection circuitry that prevents data from being written to memory when the voltage falls below 4.65 Volts. The XVME-113 also contains a battery-backed real-time clock and configuration register to enable reading of memory type and size.

X Y C O M
V M E

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PRODUCT SPECIFICATIONS AND RATINGS

Environmental

	Operating	Nonoperating
Thermal	0° to 65° C (32° to 149° F)	-40° to 85° C (-40° to 185° F)
Humidity	20% to 80% RH, noncondensing ^a	20% to 80% RH, noncondensing ^a
Shock	30g peak acceleration, 11 msec duration	50g peak acceleration, 11 msec duration
Vibration 5-2000 Hz	.006" (.15 mm) peak-to-peak displacement 2.5g maximum acceleration	.015" (.38 mm) peak-to-peak displacement 2.5g maximum acceleration
Altitude	Sea level to 10,000 ft.(3048 m)	Sea level to 40,000 ft.(12192 m)

^aextremely low humidity conditions may require special protection against static discharge

Hardware

Power supply	+5 V @ .7A typical, .9 A maximum
Battery Rating	1.9 Amp hours
Battery Life	Two years typical (using Hitachi 628128 RAM, or equivalent devices)

Memory	RAM	EPROM	Flash	EEPROM
Capacity^a	12 MB	24 MB	12 MB	12 MB
Supported Device Sizes^a	128Kx8, up to 512Kx8	128Kx8, up to 1024Kx8	128Kx8, up to 512Kx8	128Kx8, up to 512Kx8
Supported Device Speeds	50 ns, 100 ns, 150 ns, and 200 ns		50 ns, 100 ns, 150 ns, and 200 ns	

^a one bank of 16 sites, and one bank of 8 sites

VME Compliance

- Complies with VMEbus specification, IEEE 1014, Rev. C.1
- A32/A24:D32/D16/D08(EO) DTB slave (memory banks)
- 4 BUS GRANT INs connected to their respective BUS GRANT OUTs
- IACKIN connected to IACKOUT
- SYSFAIL Driver
- Form Factor: DOUBLE: 9.2" × 6.3" (233.35 mm × 160 mm)

ORDERING INFORMATION

Order Number	Description
XVME-113	Double-high RAM/ROM Memory Module

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